

First principles studies of intrinsic defects in hexagonal tungsten carbide

Chang-Song Liu

csliu@issp.ac.cn

*Institute of Solid State Physics,
Chinese Academy of Sciences
Hefei City, Anhui Province*

Outline

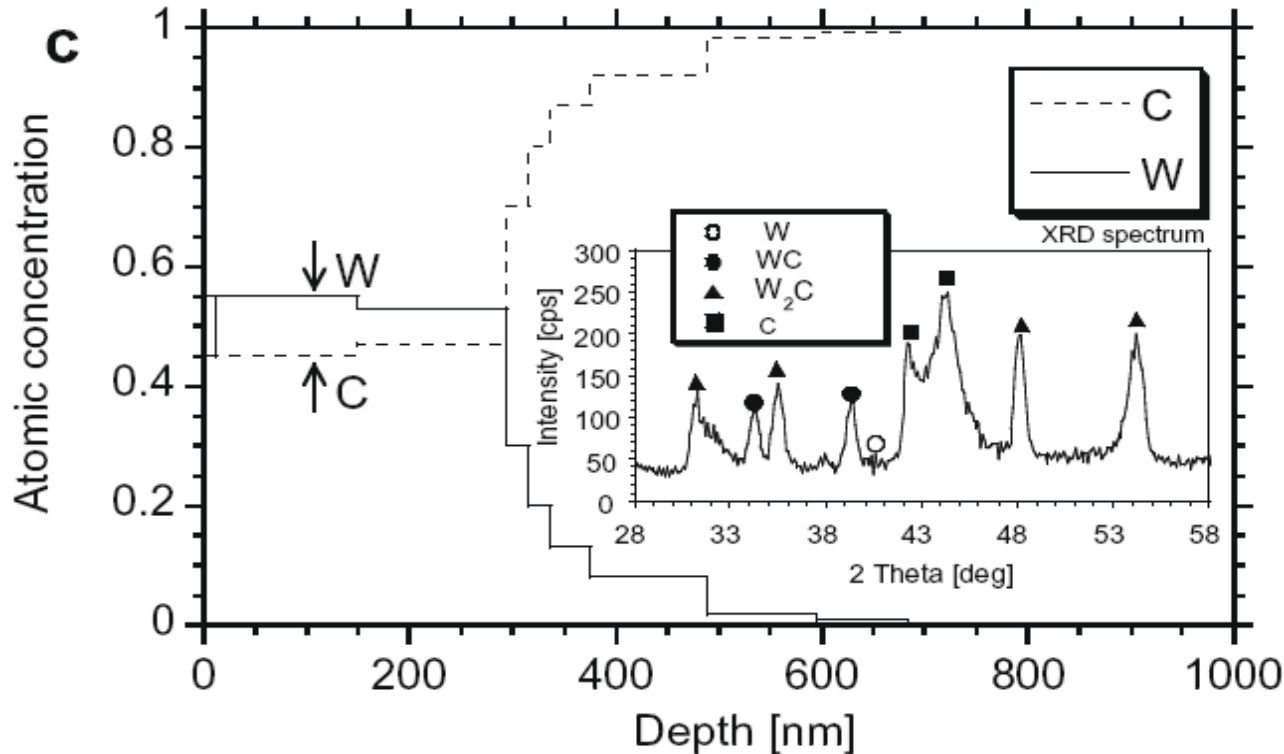
- **Background and motivation**
- **Computational methods**
- **Results and discussions**
- **Summary**

Background:

- ◆ In ITER, plasma facing materials of beryllium, carbon, and tungsten are planned to be used.
- ◆ The re-deposition of sputtered substances modifies the surface
WC is stable in a hexagonal structure, which consists of alternating simple hexagonal layers of carbon and layers of tungsten.
- ◆ For safety, periodic tritium removal is required before the in-vessel tritium inventory reaches its administrative limit, → tritium retention rate strongly affects ITER operation program in the D-T phase.
- ◆ **WC** may be used as coating materials of tungsten target of spallation neutron source.

Background: tungsten carbide

Tungsten carbide layer is formed on tungsten surface succeeding carbon impurity deposition.



Layer thickness and composition of W/C systems after annealing determined by Rutherford Backscattering Spectrometry (RBS). The XRD spectrum is shown together with RBS results. (produced by means of magnetron sputter deposition)

Background: intrinsic defects in WC

six types of intrinsic defects in WC:

- ◆ carbon (V_C) and tungsten (V_W) vacancy;
- ◆ carbon (C_W) and tungsten (W_C) antisite;
- ◆ carbon (I_C) and tungsten (I_W) interstitial.

The formation energy (eV) of intrinsic defects in WC calculated using different method.

	V_C	V_W	I_C	I_W	C_W	W_C
FPLMTO	1.77	2.72	—	—	—	—
MD	0.5	3	2.7	12	—	9.6

Big difference

FPLMTO: full-potential linear muffin-tin orbital approach

MD: molecular dynamic simulation

Medvedeva et al., PSS 43(2001)469; Juslin et al., JAP 98(2005)123520.

Background: hydrogen retention in WC

△ C films deposited by sputtering in D₂ atmosphere
□ W-C mixed films deposited by sputtering in D₂ atmosphere

--△-- 200eV D -> Pyro. Graphite

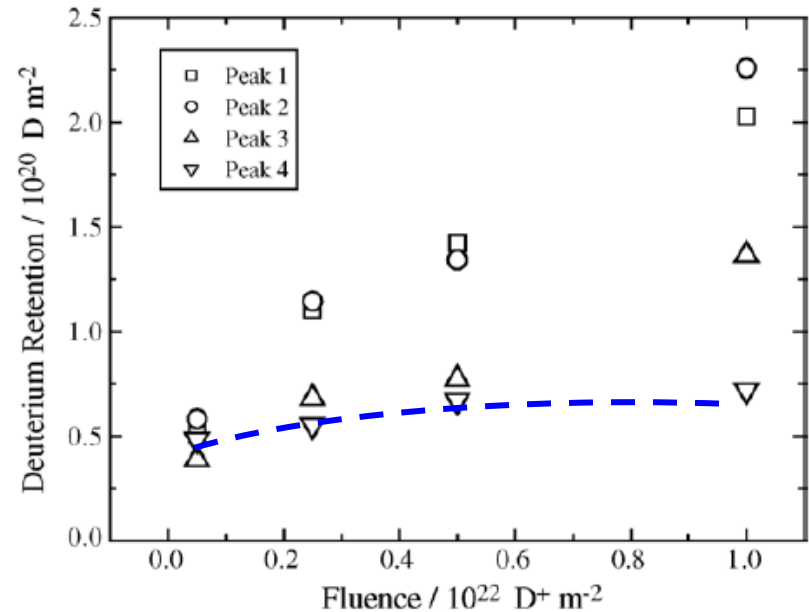
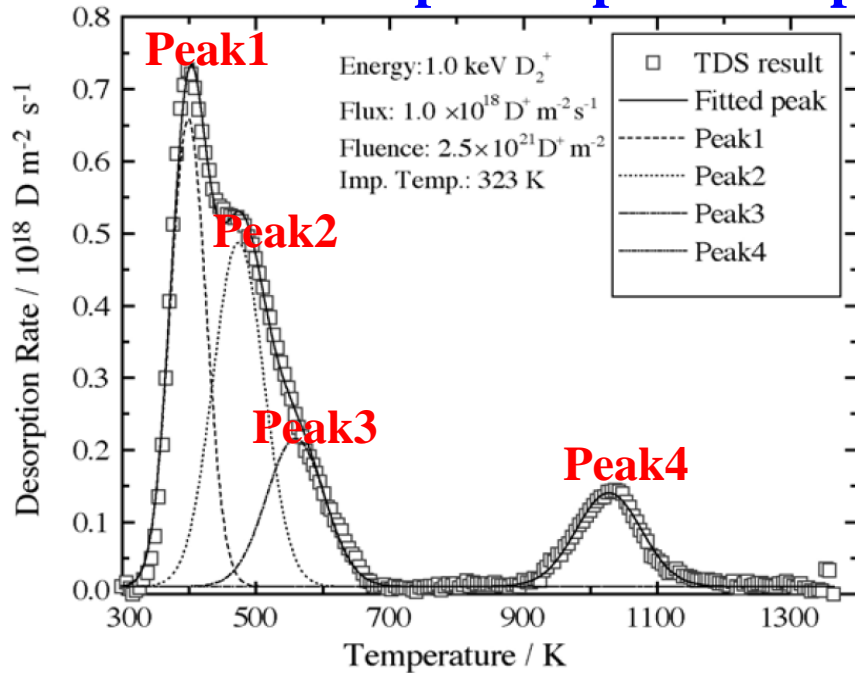
- In the WC case, the retention level seems to lie between those expected from the pure materials : $C > WC > W$.
- The property of hydrogen retention in WC are similar to that in W

Comparison of **hydrogen isotope** retention between pure carbon and tungsten surfaces to the retention in mixed W/C material

Ogorodnikova et al. J. Nucl. Mater. 313–316 (2003) 469; Igarashi et al., 363–365 (2007) 32; Sugiyama et al., 390–391 (2009) 659

Background: the desorption of hydrogen

Thermal Desorption Spectroscopy of deuterium implanted into WC



Peak 1 and 2: two different interstitial sites
Peak 3: D trapped in C vacancy
Peak 4: D bound to C

The D contention bound to carbon is very low and saturated at the initial stage of D implantation

Background: motivation

- The structure and stability of intrinsic defects of WC
- The atomic-scale mechanisms of defect migration in WC
- The trapping site of hydrogen and the interaction of hydrogen with the carbon or tungsten vacancy in WC



Computational method

- ◆ DFT (density functional theory), VASP code
- ◆ The interaction between ions and electrons: PAW
- ◆ Exchange and correlation functions: PW91-GGA
- ◆ Energy cutoff: 500 eV
- ◆ Supercell: 54-atom supercell and 128-atom supercell
- ◆ K-points: $5 \times 5 \times 5$ and $3 \times 3 \times 3$.

Results: the ground-state properties of WC

The bulk properties and cohesive energy (E_c) of WC, MD and DFT mean the results obtained by molecular dynamic simulation and density functional theory, respectively.

	$a_0(\text{nm})$	c_0/a_0	$B_0(\text{GPa})$	$E_c(\text{eV})$
Experiment	0.2907	0.976	329	-16.68
MD	0.2917	0.964	443	-16.68
DFT	0.2979	0.975	368	-15.01
Present work	0.2932	0.973	356	-16.42

Our results are in agreement with the experimental and former theoretical values



Results: vacancy and antisite defects

The formation energy of intrinsic defect:

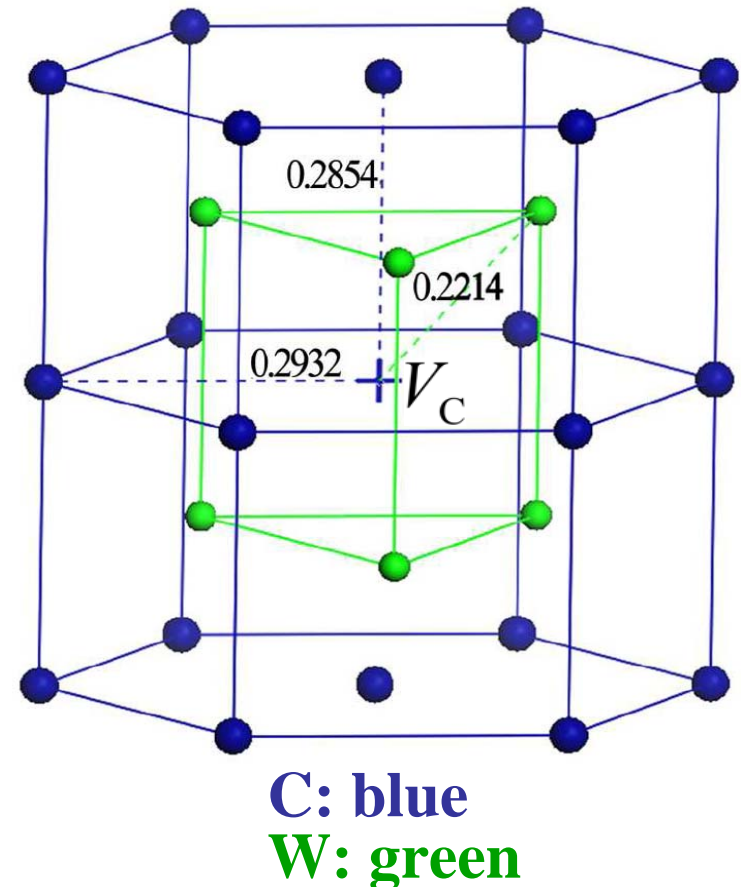
$$E_f = E - \frac{1}{2}(n_w + n_c)\mu_{wc} - \frac{1}{2}(n_w - n_c)(\mu_w - \mu_c)$$

Cohesive energy of supercell

Chemical potential of WC, W, C

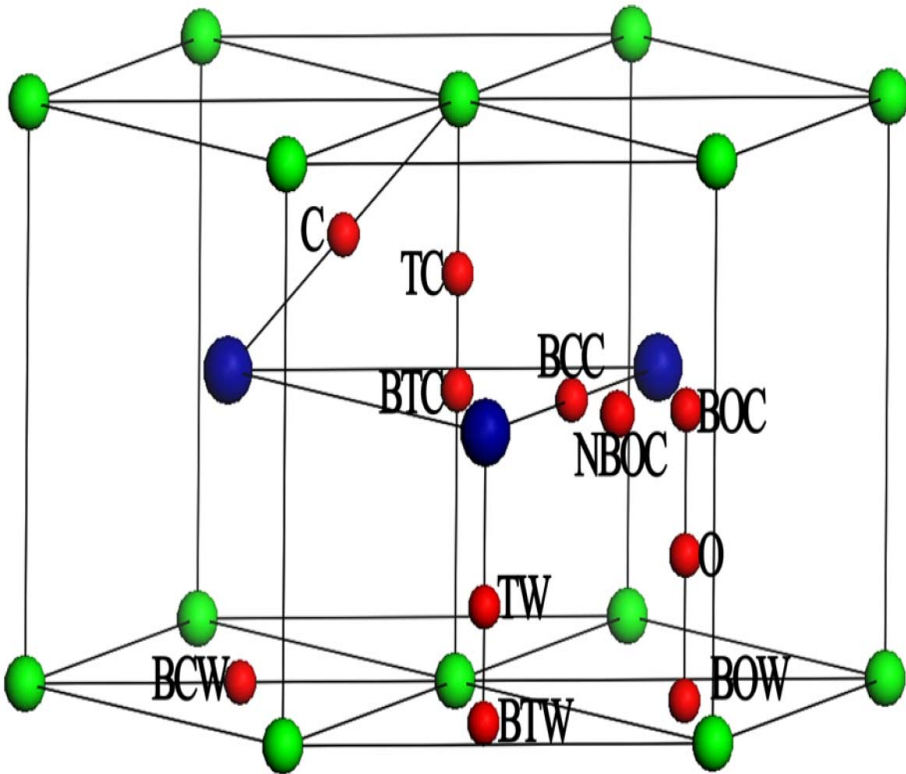
**The formation energies (eV) of
vacancies and antisites in WC**

	V_c	V_w	C_w	W_c
FPLMTO	1.77	2.72	—	—
MD	0.5	3	—	9.6
DFT	0.39	4.14	8.81	8.69





Results: interstitial defect



Interstitial sites: **red ball**

octahedral site: **O**



carbon or tungsten **basal plane**
projection of **O** site: **BOC, BOW**

two different **tetrahedral** site: **TC, TW**



BTC, BTW

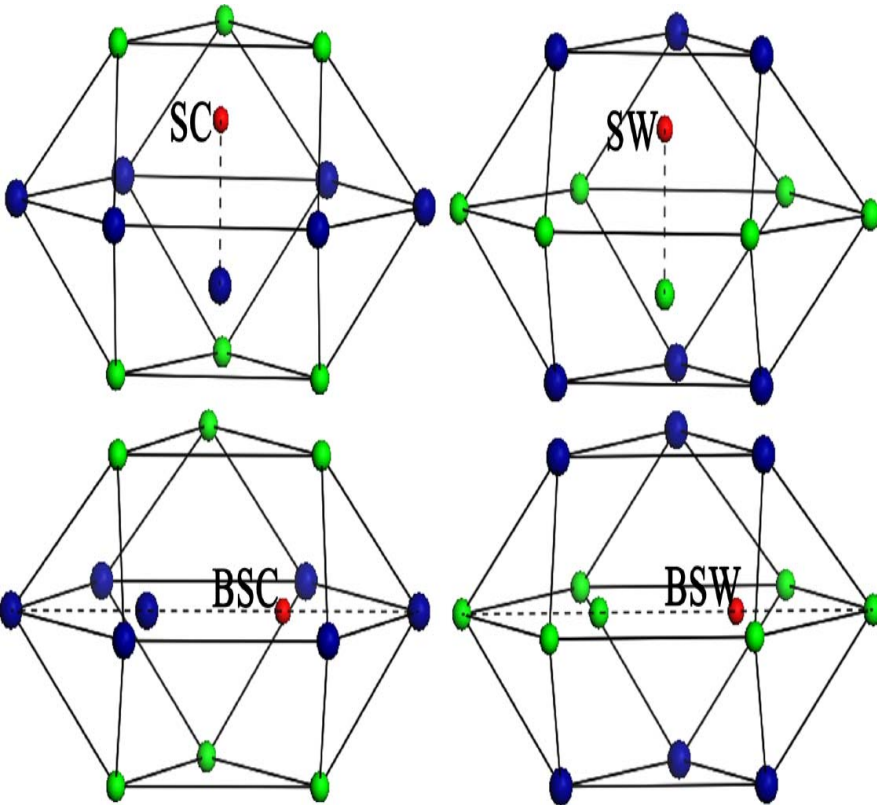
center of the nearest-neighbor
tungsten and carbon: **C**

center of the nearest-neighbor
carbon/tungsten in carbon/tungsten
basal plane: **BCC, BCW**



Results: interstitial defect

Four possible carbon/tungsten split-interstitial configurations



Two carbon/tungsten atoms are symmetrically split in the c direction: **SC/SW**

Two carbon/tungsten atoms are symmetrically split in the dense a direction about a carbon/tungsten vacant site : **BSC, BSW**

Interstitial site: **red ball**

Results: interstitial defect

The final configurations of interstitial defect in WC and corresponding formation energies (E_f), the stable configuration are highlighted in red

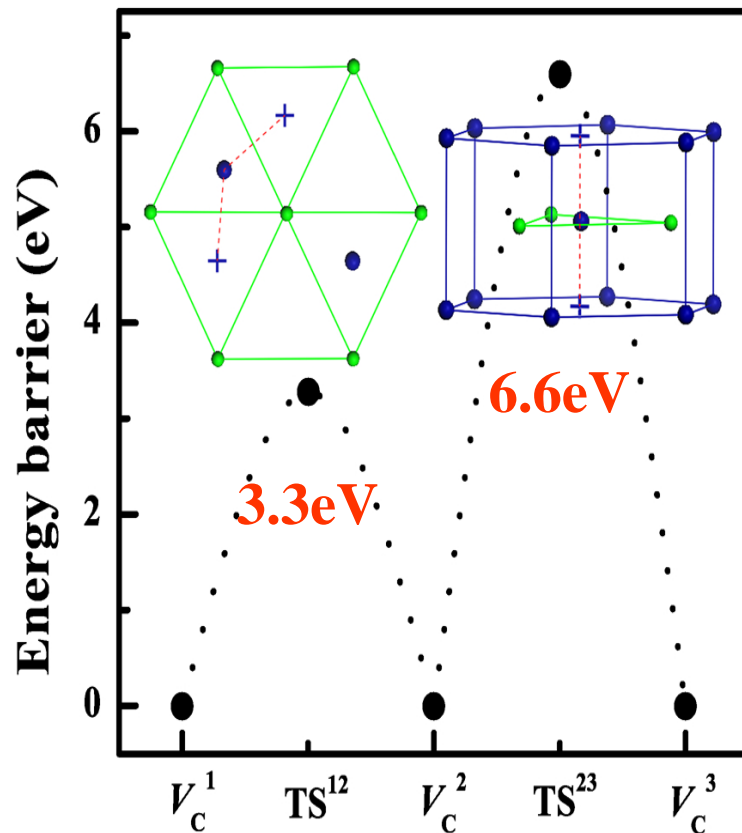
Initial site	Carbon interstitial defect		Tungsten interstitial defect	
	Final configuration	E_f	Final configuration	E_f
O	I_C (BOC)	3.41	I_W (BOC)	11.58
BOC	I_C (BOC)	3.41	I_W (BOC)	11.58
BOW	I_C (BOW)	5.00	I_W (BOW)	13.48
C	I_C (BOC)	3.41	I_C (BOC)+ W_C	9.73
BCC	I_C (BOC)	3.41	I_W (BOC)	11.58
BCW	I_C (BTW)	4.37	c -Crowdion	13.65
TC	I_C (BTC)	5.63	a -Crowdion	15.62
BTC	I_C (BTC)	5.63	a -Crowdion	15.62
TW	I_C (BTW)	4.37	I_C (BTW)+ W_C	10.65
BTW	I_C (BTW)	4.37	I_W (BTW)	15.96
SC	c -Dimer	3.53	I_C (BTW)+ W_C	10.65
SW	I_C (BTC)	5.63	c -Crowdion	13.65
BSC	a -Dimer	3.14	I_C (BOC)+ W_C	9.73
BSW	I_C (BTW)	4.37	a -Crowdion	15.62

Results(1): a brief summary

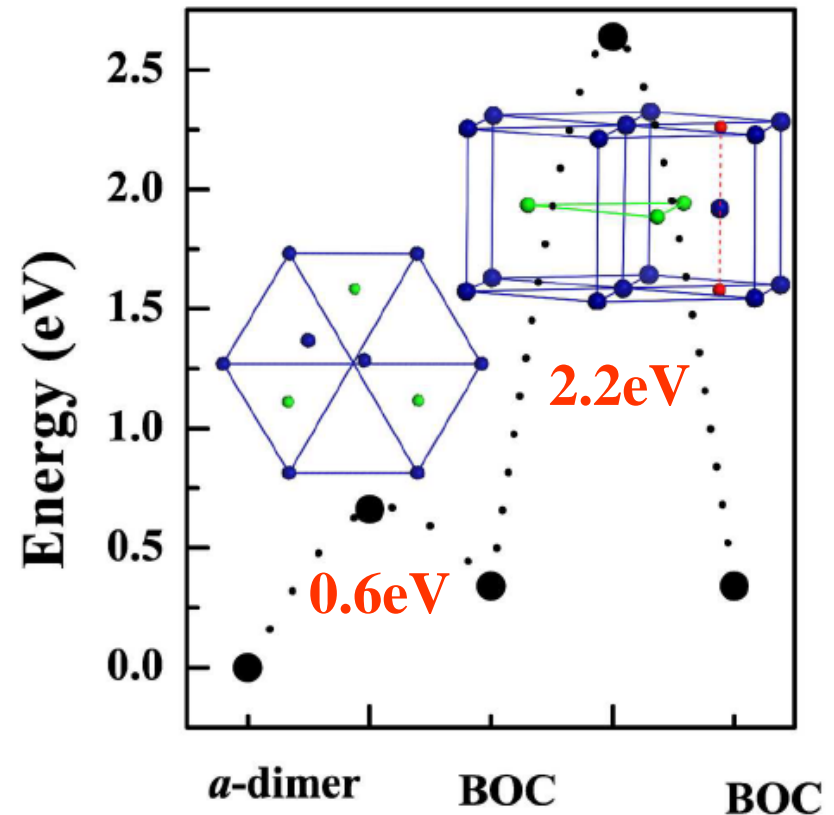
- ◆ The defect formation energy of carbon are much lower than that of tungsten.
- ◆ The carbon vacancy is the dominant defect in tungsten carbide.
- ◆ The concentration of tungsten vacancy is considerably low and the tungsten interstitial defects are energetically less favorable.
- ◆ The C-C dimer configuration along the dense a direction is the most stable configuration of carbon interstitial defect.

Results: the diffusion of carbon defect

The diffusion of carbon vacancy



The diffusion of carbon interstitial



- ◆ The energy barrier of carbon vacancy is greatly larger than that of carbon interstitial
- ◆ Both carbon vacancy and interstitial prefer to diffuse in the carbon basal plane

Results(2): a brief summary

- ◆ Formation energy: $E_f(V_C) < E_f(I_C)$;
- ◆ But diffusion energy barrier: $E_D(V_C) > E_D(I_C)$



- ◆ The carbon vacancy stay for a wide range of temperature because of extremely high diffusion barriers, while carbon interstitial migration is activated at lower temperatures for its considerably lower activation energy. Both of them prefer to **diffuse in carbon basal plane**.

Results: single H atom in WC

The defect formation energy: to identify the energy favorable trapping site of H in WC.

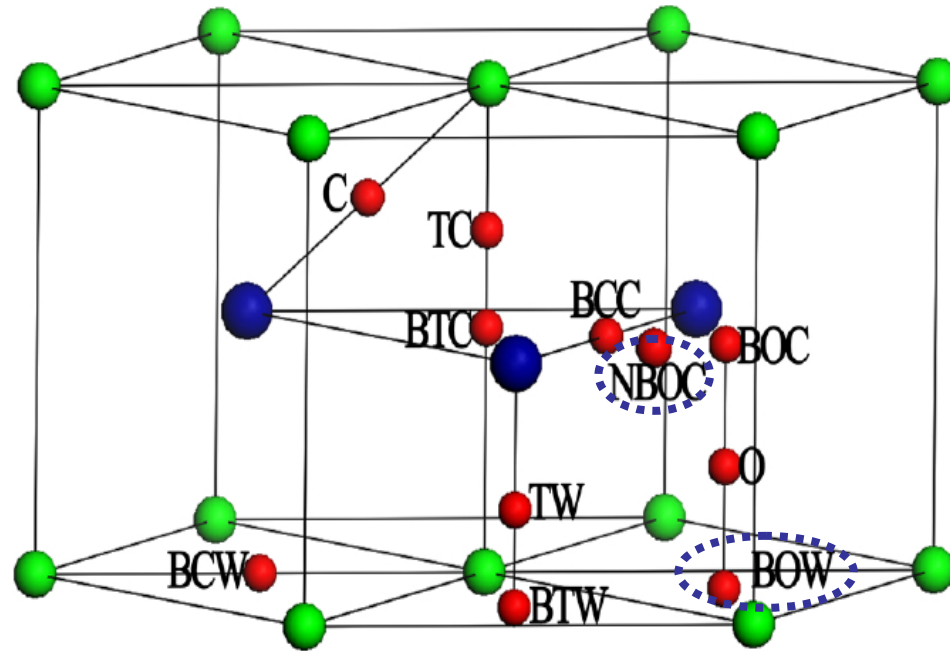
$$E_f = E_{tot}^H - E_{tot} - \mu_H$$

E_{tot} : the total energy of defect-free system

E_{tot}^H : the total energy of system with single H atom

μ_H : the hydrogen chemical potential

Results: single H atom in WC



- ◆ Two relative stable interstitial sites for H in WC: **BOW** and **NBOC**, which are different from the experimental guess (**BTW** and **BTC**). Igarashi et al., JNM 363–365 (2007) 32

Results: Double interstitial H atoms in WC

The first H: **red ball**;

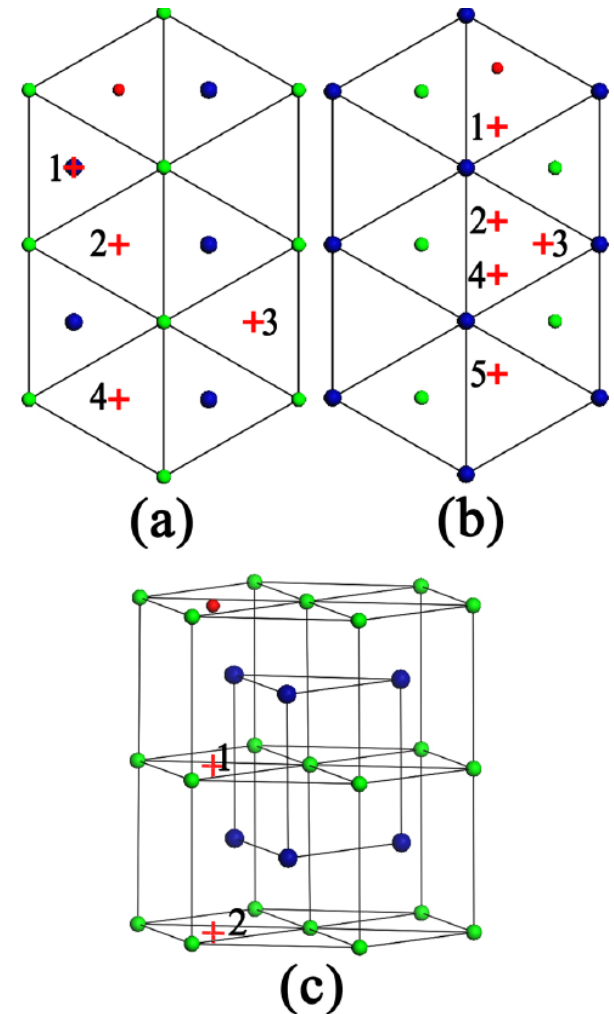
The second H: **the red +**

1~5, denote the different sites occupied by the second hydrogen atom.

(a) The first H is placed in the BOW site, and the second H is inserted at other interstitial site in the same tungsten basal plane;

(b) The first H sits in the NBOC site, and the second H occupies other interstitial site in the same carbon basal plane;

(c) Two interstitial H atoms along the c axis.



Results: Double interstitial H atoms in WC

The binding energy: to investigate the interaction of double interstitial H in WC and they form a hydrogen molecule?

negative bonding energy: repulsion between hydrogen atoms;

positive binding energy : attraction between hydrogen atoms.

$$E_b = 2E_{tot}^H - E_{tot}^{2H} - E_{tot}$$

E_{tot}^{2H} : the total energy of system with two H atoms

Results: Double interstitial H atoms in WC

The initial and final distance (before and after the relaxation, nm) between two hydrogen atoms and corresponding binding energy (eV) in three cases.

case	The second atom site	Initial distance	Final distance	Bonding energy
(a)	1	0.1681	0.1743	-1.92
	2	0.2906	0.2971	-0.18
	3	0.5033	0.5093	-0.06
	4	0.5812	0.5875	-0.06
(b)	1	0.1163	0.1444	-0.59
	2	0.2932	0.2983	-0.11
	3	0.3467	0.3503	-0.09
	4	0.3849	0.3856	-0.07
	5	0.5865	0.5866	-0.05
(c)	1	0.2838	0.2920	-0.17
	2	0.5674	0.5721	-0.02

◆ the distance between two hydrogen atoms increases

◆ the binding energy are negative

Results: Double interstitial H atoms in WC

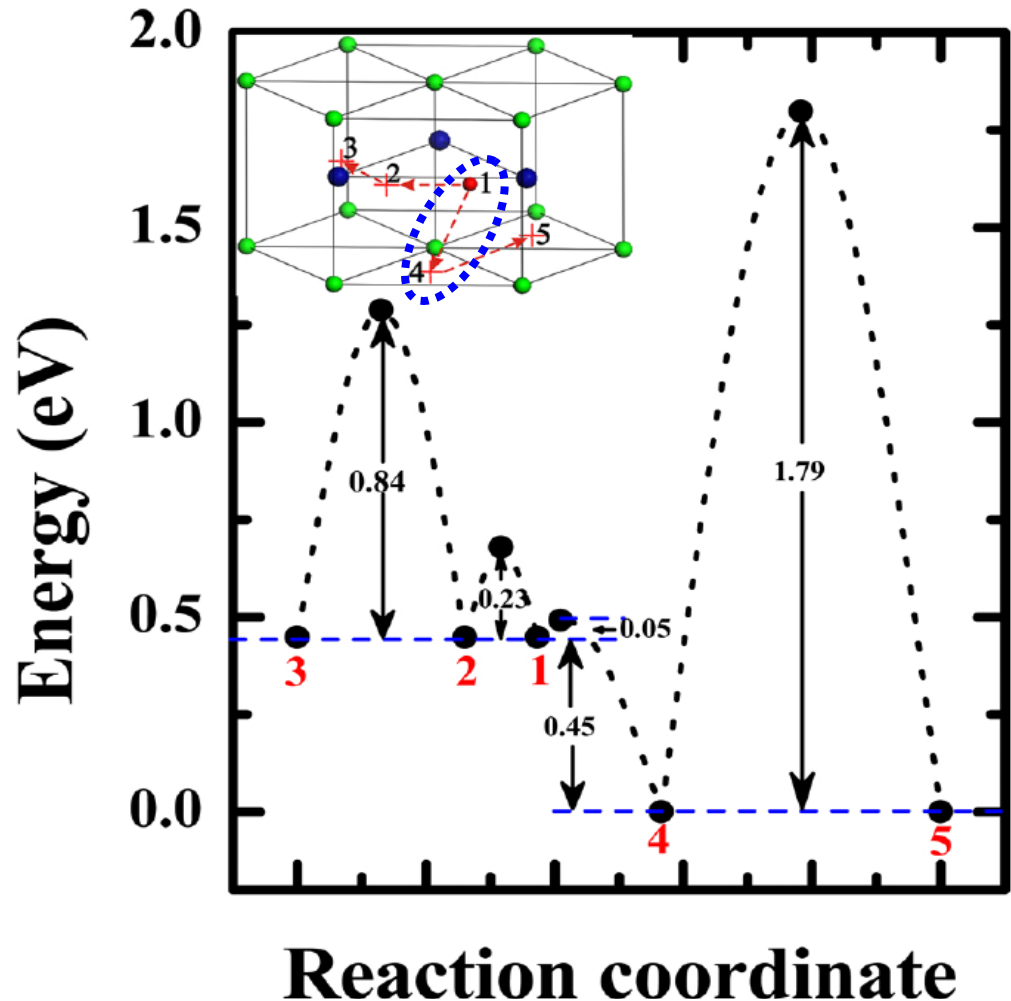
There exists a repulsive interaction
when two interstitial H atoms are close
to each other.
So they do not form H₂

Results: the diffusion of interstitial H

Diffusion energy profile and the corresponding diffusion paths for interstitial hydrogen atom in WC.

- Site 1, 2 and 3: NBOC site
- Sites 4 and 5: BOW site

The interstitial H atom prefers to jump from NBOC to BOW **along the c axis in WC**



Results(3): a brief summary

- ◆ Two stable interstitial sites for the H atom in WC are BOW and NBOC, which may be responsible for the two low temperature desorption peaks, i.e., Peak 1 and Peak 2, respectively.
- ◆ The binding energy between two interstitial hydrogen atoms is negative, suggesting that hydrogen itself is not capable of trapping other hydrogen atoms to form a hydrogen molecule.
- ◆ The interstitial hydrogen atom prefers to diffusion along the c axis

Results: multiple H occupancy of vacancy

Cumulative H trapping energy of m hydrogen atoms in a carbon/tungsten vacancy

$$E_{tr}^{mH-V_C} = E_{tot}^{mH-V_C} - E_{tot}^{V_C} - m(E_{tot}^H - E_{tot})$$

$$E_{tr}^{mH-V_W} = E_{tot}^{mH-V_W} - E_{tot}^{V_W} - m(E_{tot}^H - E_{tot})$$

The trapping energy when the number of H atoms in carbon/tungsten vacancy is increased from $m-1$ to m

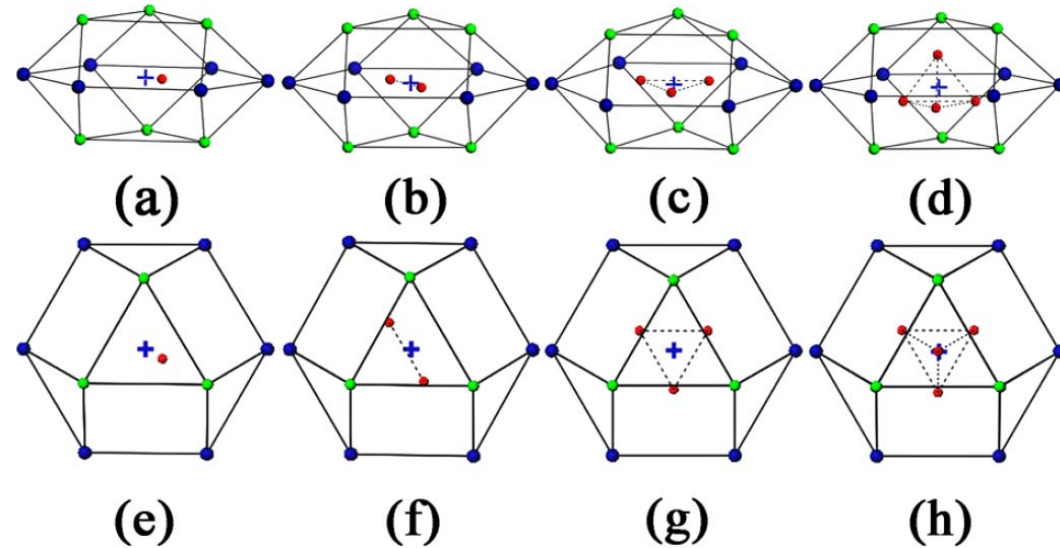
$$\Delta E_{tr}^{mH-V_C} = E_{tot}^{mH-V_C} - E_{tot}^{(m-1)H-V_C} - (E_{tot}^H - E_{tot})$$

$$\Delta E_{tr}^{mH-V_W} = E_{tot}^{mH-V_W} - E_{tot}^{(m-1)H-V_W} - (E_{tot}^H - E_{tot})$$

Negative trapping energy indicates that the addition of hydrogen atoms is energetically favorable

Results: multiple H occupancy of V_C

The schematic diagram of the lowest-energy configurations of $mH-V_C$ and the corresponding trapping energy and cumulative trapping energy (eV)



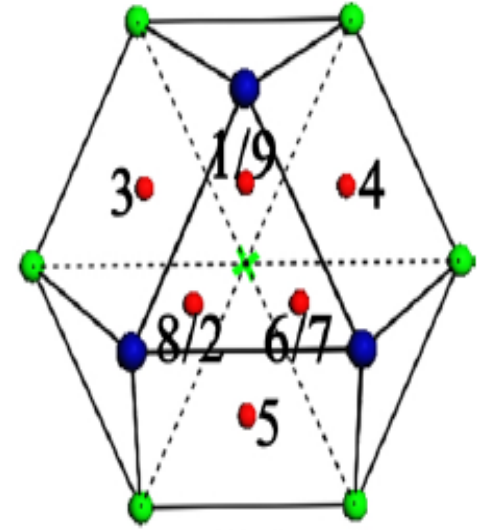
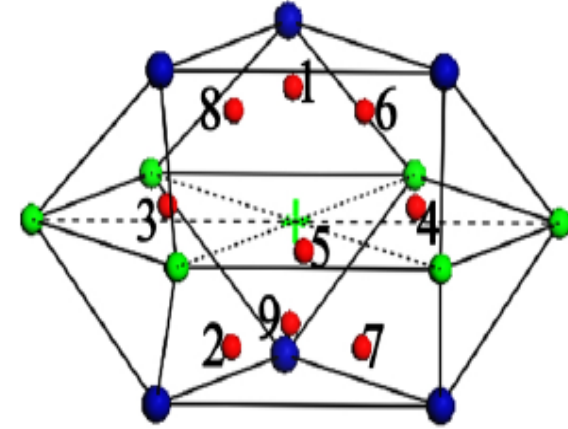
system	$\Delta E_{tr}^{mH-V_C}$	$E_{tot}^{mH-V_C}$
$1H - V_C$	-0.25	-0.25
$2H - V_C$	-0.83	-1.08
$3H - V_C$	-0.27	-1.35
$4H - V_C$	0.20	-1.15

- ◆ It is energetically favorable for mono-carbon-vacancy to trap as many as 3 H atoms.
- ◆ Hydrogen atoms can not bind together to form a H_2 in mono-carbon-vacancy.

Results: multiple H occupancy of V_W

The schematic diagram of the lowest-energy configurations of $mH-V_W$ and the corresponding trapping energy and cumulative trapping energy (eV). N_{C-H} and D_{C-H} (nm) are the number and length of C-H bond, respectively. D_{H-H} (nm) is the smallest distance between two H atoms

system	Occupied site	$\Delta E_{tr}^{mH-V_W}$	$E_{tot}^{mH-V_W}$	N_{C-H}	D_{C-H}	D_{H-H}
$1H - V_W$	1	-0.95	-0.95	1	0.116	
$2H - V_W$	1,2	-0.89	-1.85	2	0.115	0.224
$3H - V_W$	1~3	-0.93	-2.78	2	0.116	0.178
$4H - V_W$	1~4	-0.92	-3.70	2	0.116	0.174
$5H - V_W$	1~5	-0.95	-4.66	2	0.116	0.175
$6H - V_W$	1~6	-0.70	-5.36	3	0.117	0.153
$7H - V_W$	1~7	-0.62	-5.97	4	0.114	0.155
$8H - V_W$	1~8	-0.07	-6.04	5	0.114	0.149
$9H - V_W$	1~9	-0.01	-6.05	6	0.111	0.149
$10H - V_W$	1~9,sub	1.48	-4.57	6	0.113	0.129

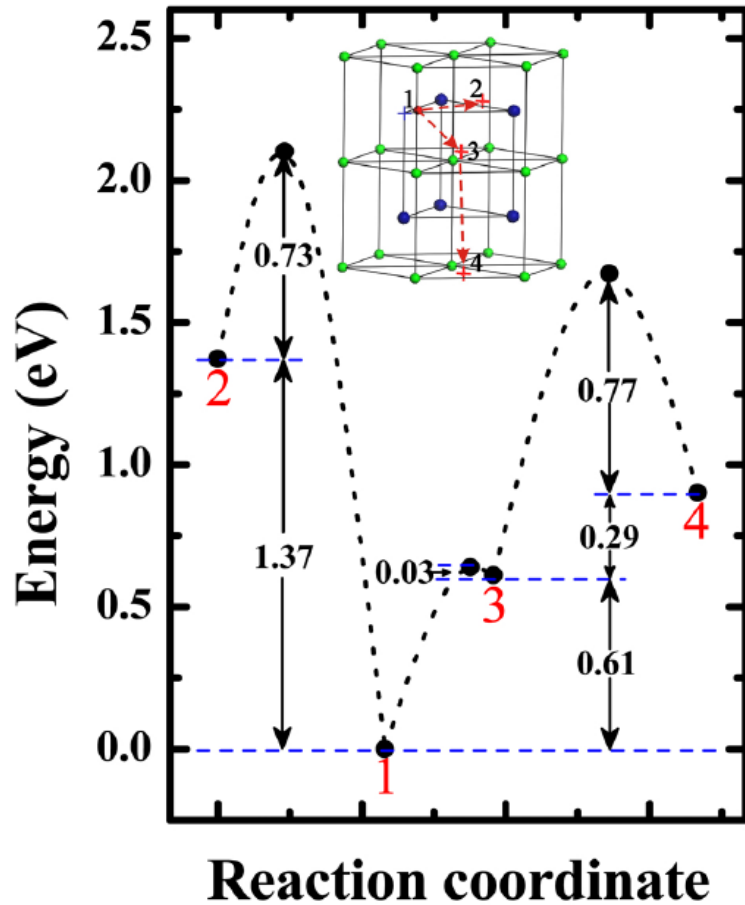


Results: multiple H occupancy of V_W

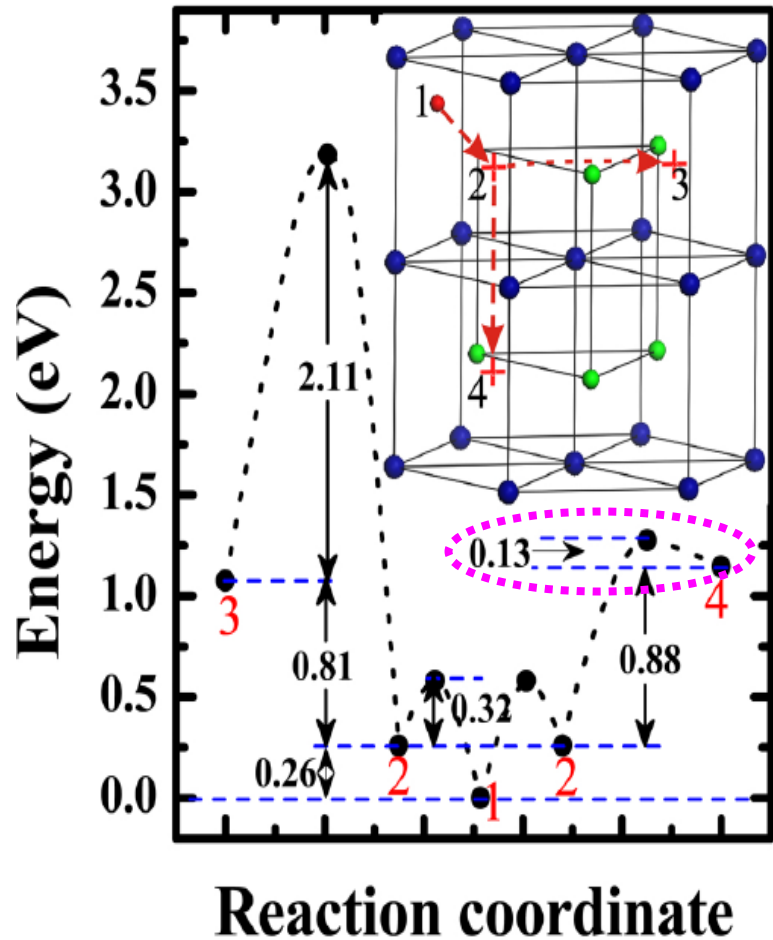
- ◆ It is energetically favorable for mono-tungsten-vacancy to trap as many as 9 H atoms.
- ◆ Hydrogen atoms can not bind together to form a H_2 in mono-tungsten-vacancy.
- ◆ The hydrogen atoms bound to carbon are only found in tungsten vacancy.

Results: the H detrapping from vacancy

H detrapping from V_C



H detrapping from V_W



Results(4): a brief summary

- ◆ It is energetically favorable for single carbon and tungsten vacancy to trap as many as 3 and 9 H atoms, respectively
- ◆ Hydrogen atoms can not bind together to form H_2 in mono-vacancy.
- ◆ The hydrogen atoms bound to carbon are only found in tungsten vacancy.
- ◆ The energy barrier of H atom jumping into the tungsten vacancy is relatively low.
- ◆ Our results provides an explanation for that the concentration of H bound to carbon is very low and saturated at the initial stage of hydrogen implantation in WC.

Summary

- ◆ The carbon vacancy is **the dominant defect** in tungsten carbide.
- ◆ The concentration of tungsten vacancy **is considerably low**.
- ◆ **Two stable interstitial sites** for the H atom in WC are BOW and NBOC, which are responsible for the two low temperature desorption peaks, i.e., Peak 1 and Peak 2, respectively.
- ◆ Hydrogen atoms can not bind together to form H_2 both in intrinsic WC and in mono-vacancy.
- ◆ The hydrogen atoms bound to carbon are only found in tungsten vacancy, and the energy barrier of H atom jumping into the tungsten vacancy is relatively low, which **provides an explanation** for that the concentration of H bound to carbon is very low and saturated at the initial stage of hydrogen implantation in WC.

Thanks for your attention!